

BGA715L7

Silicon Germanium GPS Low Noise Amplifier

Small Signal Discretes



Never stop thinking

Edition 2009-10-9

**Published by
Infineon Technologies AG
81726 München, Germany**

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Revision History: 2009-10-9, Rev.2.1

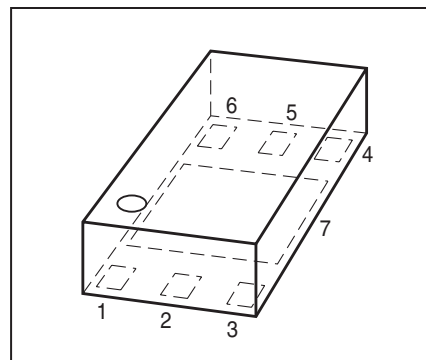
Previous Version: 2008-09-12, Rev.2.0

Data Sheet

1 Silicon Germanium GPS Low Noise Amplifier

Features

- High gain: 20 dB
- Low Noise Figure: 0.7 dB
- Low current consumption: 3.3 mA
- Supply voltage: 1.5 V to 3.3 V
- High input compression point -15.5 dBm at 1.8 V supply
- High input 3rd intercept point -7 dBm at 1.8 V supply
- B7HFM Silicon Germanium technology
- RF output internally matched to 50 Ω
- Low external part count
- 2kV HBM ESD protection (including AI-pin)
- Tiny TSLP-7-1 leadless package
- Moisture sensitivity level: MSL 1
- Pb-free (RoHS compliant) package



TSLP-7-1



Application

- 1575 MHz GPS, Galileo, GPS phone

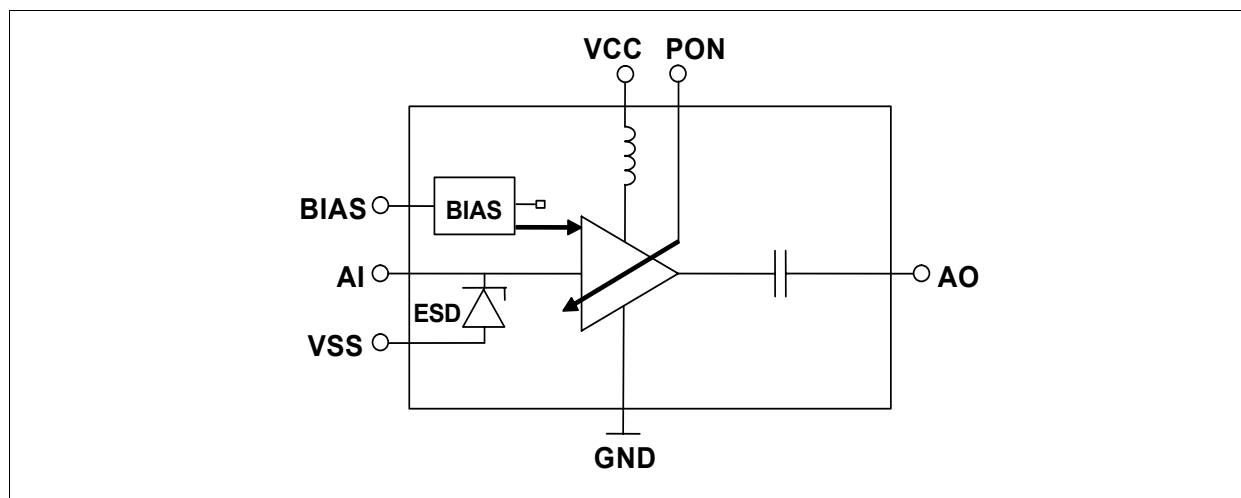


Figure 1 Blockdiagram

2 Description

The BGA715L7 is a front-end low noise amplifier for Global Positioning System (GPS) applications. The LNA provides 20 dB gain, 0.7 dB noise figure and high linearity performance in the application configuration described in [Chapter 4](#). Current consumption is as low as 3.3 mA. The BGA715L7 is based upon Infineon Technologies' B7HFM Silicon Germanium technology. It operates over a 1.5 V to 3.3 V supply range.

If an ultra low noise figure of 0.6 dB is required, please refer to Infineon BGA715L7 Application Note AN161.

Description

Type	Package	Marking
BGA715L7	TSLP-7-1	UG

Pin Definition and Function

Table 1 Pin Definition and Function

Pin No.	Symbol	Function
1	AI	LNA input
2	BIAS	DC bias
3	GND	RF ground
4	PON	Power on control
5	VCC	DC supply
6	AO	LNA output
7	VSS	DC ground

Maximum Ratings

Table 2 Maximum Ratings

Parameter ¹⁾	Symbol	Value	Unit
Voltage at pin VCC	V_{CC}	-0.3 ... 3.6	V
Voltage at pin AI	V_{AI}	-0.3 ... 0.9	V
Voltage at pin BIAS	V_{BIAS}	-0.3 ... 0.9	V
Voltage at pin AO	V_{AO}	-0.3 ... $V_{CC} + 0.3$	V
Voltage at pin PON	V_{PON}	-0.3 ... $V_{CC} + 0.3$	V
Voltage at pin GND	V_{GND}	-0.3 ... 0.3	V
Current into pin VCC	I_{CC}	10	mA
RF input power	P_{IN}	10	dBm
Total power dissipation	P_{tot}	36	mW
Junction temperature	T_J	150	°C
Ambient temperature range	T_A	-40 ... 85	°C
Storage temperature range	T_{STG}	-65 ... 150	°C
²⁾ Human Body Model ESD capability, all pin to all pin	V_{ESD_HBM}	2000	V
³⁾ Machine Model ESD capability, all pin to all pin	V_{ESD_MM}	100	V

1) All voltages refer to VSS-Node.

2) According to JEDEC22A-114

3) According to JEDEC22A-115

Thermal resistance

Table 3 Thermal resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	159	K/W

1) For calculation of R_{thJA} please refer to Application Note Thermal Resistance

3 Electrical Characteristics

Table 4 Electrical Characteristics¹⁾: $T_A = 25\text{ °C}$, $V_{CC} = 1.8\text{ V}$, $V_{PON,ON} = 1.8\text{ V}$, $V_{PON,OFF} = 0\text{ V}$, $f = 1575\text{ MHz}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply voltage	V_{CC}	1.5	1.8	3.6	V	
Supply current	I_{CC}	-	3.3	-	mA	ON-mode
		-	0.2	3	μA	OFF-mode
Gain switch control voltage	V_{pon}	1.0	-	V_{CC}	V	ON-mode
		0	-	0.4	V	OFF-mode
Gain switch control current	I_{pon}	-	5	-	μA	ON-mode
		-	-	1	μA	OFF-mode
Power gain	$ S_{21} ^2$	-	20	-	dB	High-gain Mode
Noise figure ²⁾	NF	-	0.7	-	dB	$Z_S = 50\text{ }\Omega$
Input return loss	RL_{in}	-	14	-	dB	
Output return loss	RL_{out}	-	13	-	dB	
Reverse isolation	$1/ S_{12} ^2$	-	43	-	dB	
Power gain settling time ³⁾	t_S	-	5	-	μs	OFF- to ON-mode
		-	5	-	μs	ON- to OFF-mode
Inband input 1dB compression point	IP_{1dB}	-	-15.5	-	dBm	
Inband input 3rd order intercept point ⁴⁾	IIP_3	-	-7	-	dBm	$f_1 = 1575\text{ MHz}$ $f_2 = f_1 +/-1\text{ MHz}$
Stability	k	-	> 1	-		$f = 20\text{ MHz} \dots 20\text{ GHz}$

1) Measured on BGA715L7 application board according to application schematic on page 7, including PCB losses (unless noted otherwise)

2) PCB transmission line- and connector losses of 0.05dB are subtracted

3) To be within 1 dB of the final gain OFF- to ON-mode; to be within 3 dB of the final gain ON- to OFF-mode

4) Input Power = -30 dBm for each tone

4 Application Information

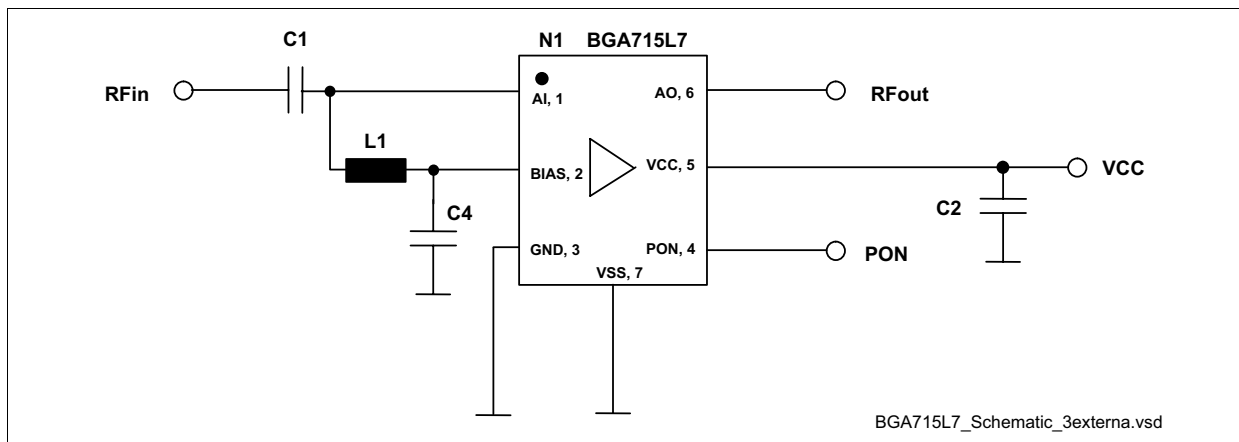


Figure 2 Application Schematic BGA715L7

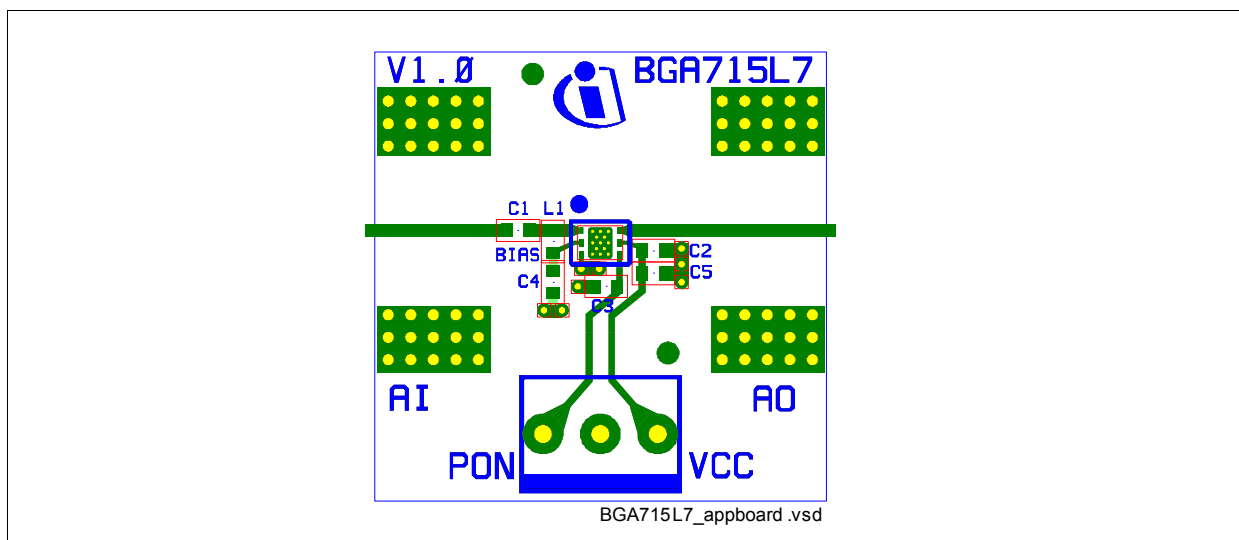


Figure 3 Application Board Drawing BGA715L7

Table 5 Bill of Materials

Name	Value	Package	Manufacturer	Function
C1	1.8 pF	0402	Various	DC blocking and input matching
C2	1 μ F	0402	Various	RF block
C4	15 pF	0402	Various	RF block
L1	4.7 nH LQW15A series	0402	Murata	Bias feed and input matching
N1	BGA715L7	TSLP-7-1	Infineon	SiGe LNA

A list of all application notes is available at <http://goto.infineon.com/smallsignaldiscretes-appnotes>.

